

200mA 40V(0.30mm)

### Chip Information

Chip Size	0.30 x 0.30mm
Pad Size	0.13 x 0.13mm
Chip Quantity	122959 pcs/wafer
Scribe Line Width	60um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

### MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	40	V	
Average Forward Rectified Current	IF(AV)	200	mA	
Peak Forward Surge Current	IFSM	0.6	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

### ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.380	0.375	0.352	V	IF=1mA Ta=25degC
	VF2	1.000	0.980	0.770	V	IF=40mA Ta=25degC
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	0.2	0.18	0.025	uA	VR=30V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	42	45	55	V	IR=10uA
Junction Capacitance	Cj	5		2.7	pF	V=0V,f=1MHz
Reverse Recovery Time	trr	5		1	nS	IF=IR=10mA irr=0.1IR

### Ordering Information

Chip Type	Chip Thickness	Back Metal
XHP035	180 +/- 20um	Au(For Eutectic)
XHP037	150 +/- 20um	Au(For Eutectic)
XHP036	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:  
Designed For BAS40